MMIC wideband amplifier

Rev. 5 — 3 October 2016

Product data sheet

1. Product profile

1.1 General description

Silicon Monolithic Microwave Integrated Circuit (MMIC) wideband amplifier with internal matching circuit in a 6-pin SOT363 plastic SMD package.

1.2 Features and benefits

- Internally matched to 50 Ω
- A gain of 26.4 dB at 2150 MHz
- Output power at 1 dB gain compression = 8 dBm
- Supply current = 21.7 mA at a supply voltage of 5.0 V
- Reverse isolation > 37 dB up to 2150 MHz
- Good linearity with low second order and third order products
- Noise figure = 3.6 dB at 950 MHz
- Unconditionally stable (K > 1)
- No output inductor required

1.3 Applications

- LNB IF amplifiers
- General purpose low noise wideband amplifier for frequencies between DC and 2.2 GHz

2. Pinning information

Pin	Description	Simplified outline	Graphic symbol
1	V _{CC}		
2, 5	GND2		
3	RF_OUT		6
4	GND1		
6	RF_IN		4 2, 5 777 777 sym052



3. Ordering information

Table 2. Ordering information							
Type number Package							
	Name	Description	Version				
BGA2867	-	plastic surface-mounted package; 6 leads	SOT363				

4. Marking

Type number	Marking code	Description
BGA2867	LP*	* = - : made in Hong Kong
		* = p : made in Hong Kong
		* = W : made in China
		* = t : made in Malaysia

5. Limiting values

Table 4.Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V _{CC}	supply voltage	RF input AC coupled	-0.5	+7.0	V
I _{CC}	supply current		-	36	mA
P _{tot}	total power dissipation	T _{sp} = 90 °C	-	200	mW
T _{stg}	storage temperature		-40	+125	°C
Tj	junction temperature		-	125	°C
P _{drive}	drive power		-	+10	dBm

6. Thermal characteristics

Table 5.	Thermal characteristics					
Symbol	Parameter	Conditions	Тур	Unit		
R _{th(j-sp)}	thermal resistance from junction to solder point	P_{tot} = 200 mW; T_{sp} = 90 °C	300	K/W		

7. Characteristics

Table 6.Characteristics

 $V_{CC} = 5 V; Z_S = Z_L = 50 \Omega; P_i = -34 dBm; T_{amb} = 25$ °C; measured on demo board; unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{CC}	supply voltage		4.5	5.0	5.5	V
I _{CC}	supply current		20.1	21.7	23.2	mA

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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Gp	power gain	f = 250 MHz	25.8	26.3	26.9	dB
		f = 950 MHz	26.4	27.1	27.8	dB
		f = 2150 MHz	24.9	26.4	27.9	dB
RL _{in}	input return loss	f = 250 MHz	19	21	23	dB
	L _{in} input return loss	f = 950 MHz	18	20	22	dB
		f = 2150 MHz	19	25	31	dB
RL _{out}	output return loss	f = 250 MHz	13	17	21	dB
		f = 950 MHz	17	18	19	dB
		f = 2150 MHz	12	14	17	dB
ISL	isolation	f = 250 MHz	44	64	84	dB
		f = 950 MHz	44	46	48	dB
		f = 2150 MHz	34	37	39	dB
NF	noise figure	f = 250 MHz	3.2	3.7	4.2	dB
		f = 950 MHz	3.2	3.6	4.1	dB
		f = 2150 MHz	3.3	3.8	4.2	dB
B _{-3dB}	-3 dB bandwidth	3 dB below gain at 1 GHz	2.8	3	3.2	GHz
K	Rollett stability factor	f = 250 MHz	29	36	38	
		f = 950 MHz	3.5	4.5	4.5	
		f = 2150 MHz	1	1.8	2.8	
P _{L(sat)}	saturated output power	f = 250 MHz	8	9	9	dBm
		f = 950 MHz	7	8	10	dBm
		f = 2150 MHz	5	6	7	dBm
P _{L(1dB)}	output power at 1 dB gain compression	f = 250 MHz	6	7	8	dBm
		f = 950 MHz	5	7	8	dBm
		f = 2150 MHz	4	5	6	dBm
IP3 _I	input third-order intercept point	$P_{drive} = -40 \text{ dBm}$ (for each tone)				
		f ₁ = 250 MHz; f ₂ = 251 MHz	-7	-5	-3	dBm
		f ₁ = 950 MHz; f ₂ = 951 MHz	-11	-8	-6	dBm
		f ₁ = 2150 MHz; f ₂ = 2151 MHz	-16	-13	-10	dBm
IP3 ₀	output third-order intercept point	$P_{drive} = -40 \text{ dBm}$ (for each tone)				
		f ₁ = 250 MHz; f ₂ = 251 MHz	19	21	23	dBm
		f ₁ = 950 MHz; f ₂ = 951 MHz	17.5	19.5	21.5	dBm
		f ₁ = 2150 MHz; f ₂ = 2151 MHz	11	14	17	dBm
P _{L(2H)}	second harmonic output power	P _{drive} = -37 dBm				
		f _{1H} = 250 MHz; f _{2H} = 500 MHz	-63	-61	-59	dBm
		f _{1H} = 950 MHz; f _{2H} = 1900 MHz	-	-50	-	dBm
∆IM2	second-order intermodulation distance	P _{drive} = -40 dBm (for each tone)				1
		f ₁ = 250 MHz; f ₂ = 251 MHz	49	51	53	dBc
		f ₁ = 950 MHz; f ₂ = 951 MHz	-	51	-	dBc

Table 6.Characteristics ...continued $V_{CC} = 5 V; Z_S = Z_l = 50 \Omega; P_l = -34 \text{ dBm}; T_{al}$

= 25 °C: measured on demo board: unless otherwise specified

8. Application information

<u>Figure 1</u> shows a typical application circuit for the BGA2867 MMIC. The device is internally matched to 50 Ω , and therefore does not need any external matching. The value of the input and output DC blocking capacitors C2 and C3 should not be more than 100 pF for applications above 100 MHz. However, when the device is operated below 100 MHz, the capacitor value should be increased.

The location of the 470 pF supply decoupling capacitor (C_{dec}) can be precisely chosen for optimum performance.

The PCB top ground plane, connected to pins 2, 4 and 5 must be as close as possible to the MMIC, preferably also below the MMIC. When using via holes, use multiple via holes as close as possible to the MMIC.



8.1 Application examples



8.2 Tables

Table 7.Supply current over temperature and supply voltagesTypical values.

Symbol	Parameter	Conditions	T _{amb} (°C	T _{amb} (°C)		
			-40	+25	+85	
I _{CC}	supply current	$V_{CC} = 4.5 V$	21.90	20.10	18.60	mA
		$V_{CC} = 5.0 V$	23.50	21.70	20.10	mA
		$V_{CC} = 5.5 V$	25.00	23.20	21.60	mA

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Symbol	Parameter	Conditions	T _{amb} (°C)		s T _{amb} (°C)	Unit	Unit
			-40	+25	+85		
P _{L(2H)}	second harmonic output power	f = 250 MHz; P_{drive} = -37 dBm					
		V _{CC} = 4.5 V	-75	-67	-62	dBm	
		V _{CC} = 5.0 V	-63	-61	-58	dBm	
		V _{CC} = 5.5 V	-59	-58	-56	dBm	
		f = 950 MHz; P_{drive} = -37 dBm					
		V _{CC} = 4.5 V	-51	-51	-50	dBm	
		V _{CC} = 5.0 V	-50	-50	-49	dBm	
		V _{CC} = 5.5 V	-49	-49	-48	dBm	

 Table 8.
 Second harmonic output power over temperature and supply voltages

 Typical values.
 Second harmonic output power over temperature and supply voltages

Table 9.	Input power at 1 dB gain compression over temperature and supply voltages
Typical val	ues.

Symbol	Parameter	Conditions	T _{amb}	T _{amb} (°C)			
			-40	+25	+85		
P _{i(1dB)}	input power at 1 dB gain compression	f = 250 MHz					
		$V_{CC} = 4.5 V$	-19	-19	-19	dBm	
		$V_{CC} = 5.0 V$	-18	-19	-19	dBm	
		$V_{CC} = 5.5 V$	-18	-18	-19	dBm	
		f = 950 MHz					
		$V_{CC} = 4.5 V$	-20	-20	-20	dBm	
		$V_{CC} = 5.0 V$	-19	-20	-20	dBm	
		$V_{CC} = 5.5 V$	-19	-19	-20	dBm	
		f = 2150 MHz					
		$V_{CC} = 4.5 V$	-21	-22	-23	dBm	
		V _{CC} = 5.0 V	-21	-22	-23	dBm	
		V _{CC} = 5.5 V	-21	-22	-23	dBm	

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Symbol	Parameter	Conditions	T _{amb} (°C)			Unit
			-40	+25	+85	
P _{L(1dB)}	output power at 1 dB gain compression	f = 250 MHz				
		$V_{CC} = 4.5 V$	7	6	5	dBm
		$V_{CC} = 5.0 V$	7	7	6	dBm
		V _{CC} = 5.5 V	8	8	7	dBm
		f = 950 MHz				
		$V_{CC} = 4.5 V$	6	6	5	dBm
		$V_{CC} = 5.0 V$	7	7	6	dBm
		V _{CC} = 5.5 V	8	7	6	dBm
		f = 2150 MHz				
		$V_{CC} = 4.5 V$	5	4	2	dBm
		$V_{CC} = 5.0 V$	6	5	3	dBm
		V _{CC} = 5.5 V	7	5	3	dBm

 Table 10.
 Output power at 1 dB gain compression over temperature and supply voltages

 Typical values.

Table 11.Saturated output power over temperature and supply voltagesTypical values.

Symbol	Parameter	Conditions	T _{amb}	T _{amb} (°C)		
			-40	+25	+85	
P _{L(sat)}	saturated output power	f = 250 MHz				
		$V_{CC} = 4.5 V$	8	8	8	dBm
		$V_{CC} = 5.0 V$	10	9	8	dBm
		$V_{CC} = 5.5 V$	10	10	9	dBm
		f = 950 MHz				
		$V_{CC} = 4.5 V$	8	8	7	dBm
		$V_{CC} = 5.0 V$	9	8	8	dBm
		$V_{CC} = 5.5 V$	10	9	8	dBm
		f = 2150 MHz				
		$V_{CC} = 4.5 V$	6	5	4	dBm
		$V_{CC} = 5.0 V$	7	6	4	dBm
		$V_{CC} = 5.5 V$	8	6	5	dBm

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Symbol	Parameter	Conditions	T _{amb} (°C)			Unit
			-40	+25	+85	
∆IM2 second-order intermodula	second-order intermodulation distance					
		$V_{CC} = 4.5 V$	43	46	51	dBc
		$V_{CC} = 5.0 V$	48	51	58	dBc
		$V_{CC} = 5.5 V$	52	56	69	dBc
		$f_1 = 950 \text{ MHz};$ $f_2 = 951 \text{ MHz};$ $P_{drive} = -40 \text{ dBm}$				
		$V_{CC} = 4.5 V$	40	45	55	dBc
		$V_{CC} = 5.0 V$	45	51	63	dBc
		$V_{CC} = 5.5 V$	50	60	52	dBc

 Table 12.
 Second-order intermodulation distance over temperature and supply voltages

 Typical values.
 Values.

Table 13.	Output third-order intercept point over temperature and supply voltages
Typical val	ues.

Symbol	Parameter	Conditions	T _{amb} (°C)			Unit
			-40	+25	+85	
IP3 ₀	output third-order intercept point	$f_1 = 250 \text{ MHz};$ $f_2 = 251 \text{ MHz};$ $P_{drive} = -40 \text{ dBm}$				
		$V_{CC} = 4.5 V$	21	19	18	dBm
		$V_{CC} = 5.0 V$	23	21	20	dBm
		V _{CC} = 5.5 V	24	23	21	dBm
		$f_1 = 950 \text{ MHz};$ $f_2 = 951 \text{ MHz};$ $P_{drive} = -40 \text{ dBm}$				
		$V_{CC} = 4.5 V$	18	17	16	dBm
		$V_{CC} = 5.0 V$	20.5	19.5	18.5	dBm
		V _{CC} = 5.5 V	21	20	18	dBm
		$f_1 = 2150 \text{ MHz};$ $f_2 = 2151 \text{ MHz};$ $P_{drive} = -40 \text{ dBm}$				
		$V_{CC} = 4.5 V$	14	13	11	dBm
		V _{CC} = 5.0 V	16	14	12	dBm
		$V_{CC} = 5.5 V$	17	15	12	dBm

Table 14.	-3 dB bandwidth over temperature and supply voltages
Typical valu	les.

Symbol	Parameter	Conditions	T _{amb} (°C)		onditions T _{amb} (°C)	Unit
			-40	+25	+85	
B _{-3dB} -		$V_{CC} = 4.5 V$	3.09	2.98	2.84	GHz
		V _{CC} = 5.0 V	3.11	3.00	2.91	GHz
		V _{CC} = 5.5 V	3.13	3.01	2.93	GHz

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9. Test information



Table 15. List of components used for the typical application

Component	Description	Value	Dimensions	Remarks
C1, C2	multilayer ceramic chip capacitor	470 pF	0603	X7R RF coupling capacitor
P5 to P24 [1]	position for multilayer ceramic chip capacitor C_{dec}	470 pF	0603	X7R RF decoupling capacitor
IC1	BGA2867 MMIC	-	SOT363	

[1] For decoupling a decoupling capacitor (C_{dec}) is used on one of the positions of P5 to P24. The results mentioned in this data sheet have been obtained using the decoupling capacitor C_{dec} on position P22.

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10. Package outline



Fig 5. Package outline SOT363

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11. Abbreviations

Table 16. Abbreviations				
Acronym	Description			
IF	Intermediate Frequency			
LNA	Low-Noise Amplifier			
LNB	Low-Noise Block converter			
PCB	Printed-Circuit Board			
SMD	Surface Mounted Device			

12. Revision history

Table 17.Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes		
BGA2867 v.5	20161003	Product data sheet	-	BGA2867 v.4		
Modifications:	 <u>Table 6 on page 2</u>: the min/max value for P_{L(2H)} (f_{1H} = 950 MHz; f_{2H} = 1900 MHz) removed <u>Table 6 on page 2</u>: the min/max value for ∆IM2 (f₁ = 950 MHz; f₂ = 951 MHz) has been removed 					
BGA2867 v.4	20150713	Product data sheet	-	BGA2867 v.3		
Modifications:	 The format of this data sheet has been redesigned to comply with the new identity guidelines of NXP Semiconductors. Legal texts have been adapted to the new company name where appropriate. 					
BGA2867 v.3	20130827	Product data sheet	-	BGA2867 v.2		
BGA2867 v.2	20120925	Product data sheet	-	BGA2867 v.1		
BGA2867 v.1	20120312	Product data sheet	-	-		

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Document status[1][2]	Product status ^[3]	Definition
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